

## Features

- Low On-Resistance
- Low Gate Threshold Voltage  $V_{GS(th)} < 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 2)**
- **ESD Protected Gate**
- **"Green" Device (Note 3)**

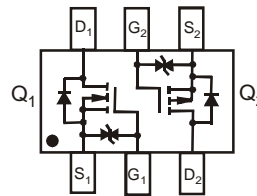
## Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 7
- Ordering & Date Code Information: See Page 7
- Weight: 0.006 grams (approximate)



TOP VIEW

SOT-363



TOP VIEW

Internal Schematic

## Maximum Ratings N-CHANNEL – Q<sub>1</sub> @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 8$	V
Drain Current (Note 1)	$I_D$	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C 540 390	mA

## Maximum Ratings P-CHANNEL – Q<sub>2</sub> @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 8$	V
Drain Current (Note 1)	$I_D$	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C -430 -310	mA

## Thermal Characteristics – Total Device @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	$P_d$	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	$T_j, T_{STG}$	-65 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB.
  2. No purposefully added lead.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).

**Electrical Characteristics N-CHANNEL – Q<sub>1</sub>** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	± 1	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.4	0.55	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 540mA
		—	0.5	0.70		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 500mA
		—	0.7	0.90		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 350mA
Forward Transfer Admittance	Y <sub>fs</sub>	200	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Diode Forward Voltage (Note 4)	V <sub>SD</sub>	0.5	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	—	150	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	20	pF	

**Electrical Characteristics P-CHANNEL – Q<sub>2</sub>** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	± 1.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.7	0.9	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -430mA
		—	1.1	1.4		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
		—	1.7	2.0		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -150mA
Forward Transfer Admittance	Y <sub>fs</sub>	200	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Diode Forward Voltage (Note 4)	V <sub>SD</sub>	-0.5	—	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -115mA
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	—	175	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	30	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	20	pF	

Notes: 4. Short duration pulse test used to minimize self-heating effect.

**Q<sub>1</sub>, N-CHANNEL**

NEW PRODUCT

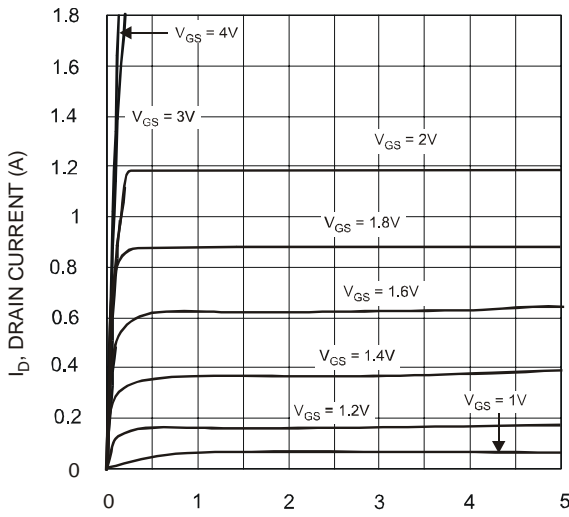


Fig. 1 Typical Output Characteristics

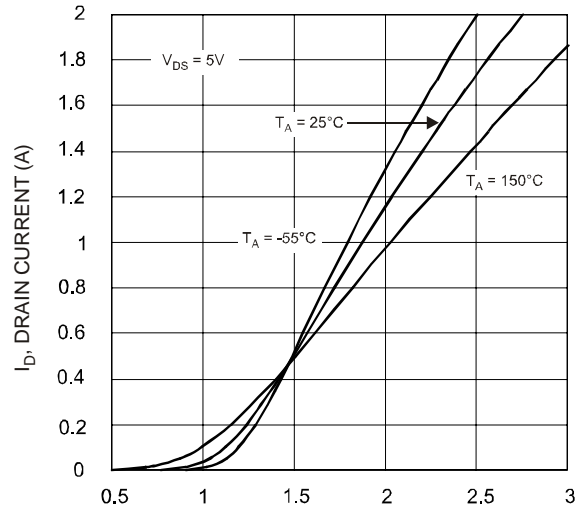


Fig. 2 Typical Transfer Characteristics

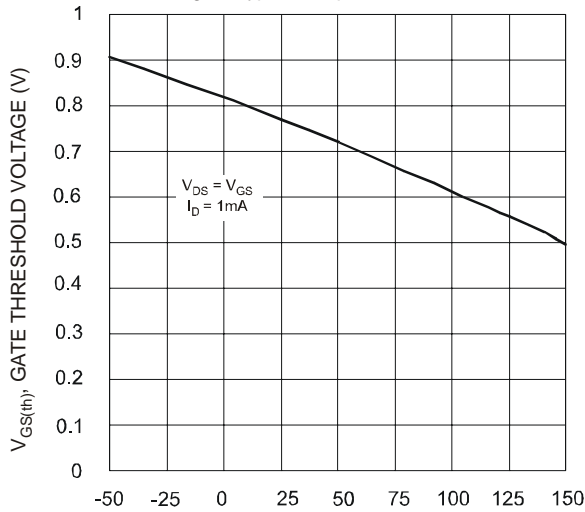


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

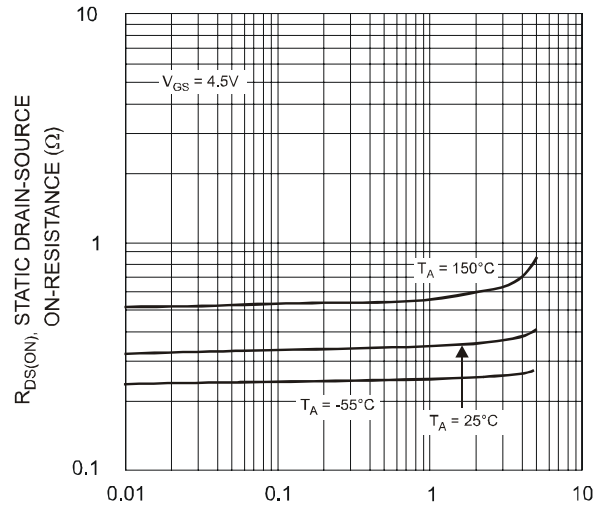


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

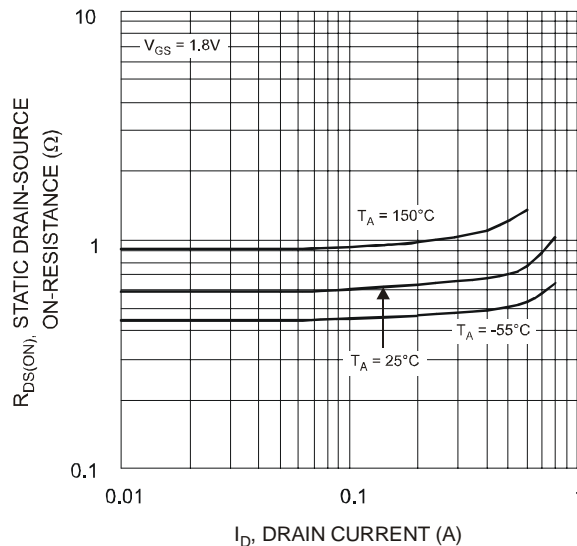


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

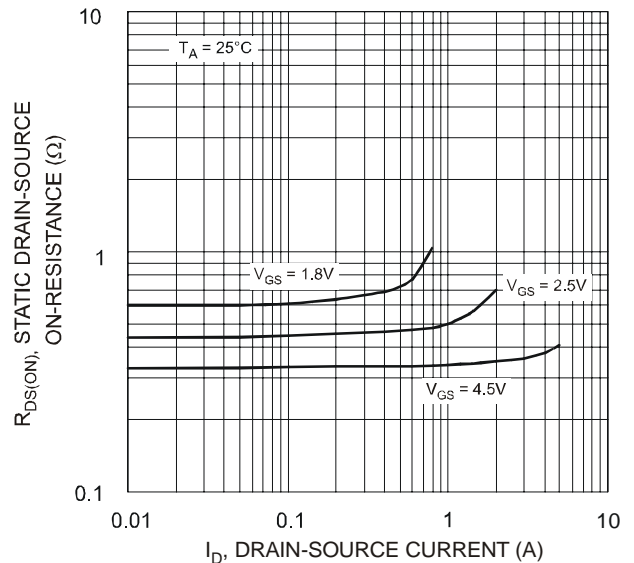


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

**Q1, N-CHANNEL, continued**

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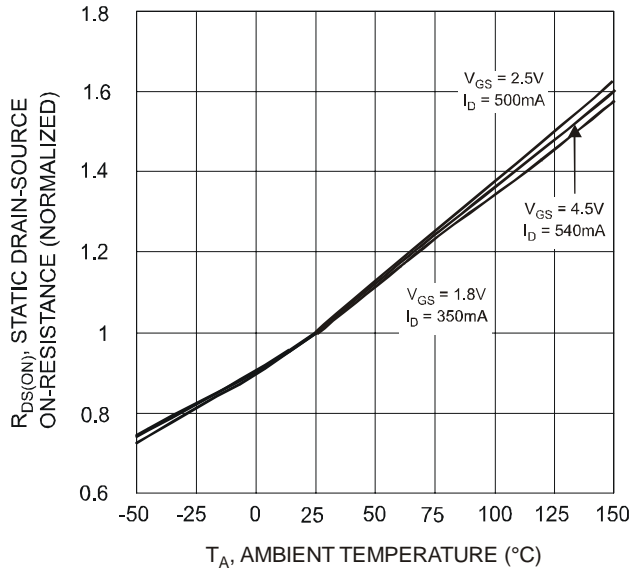


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

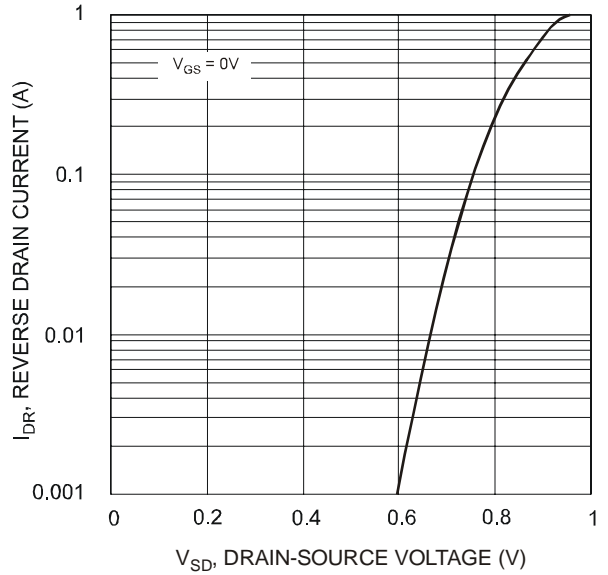


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

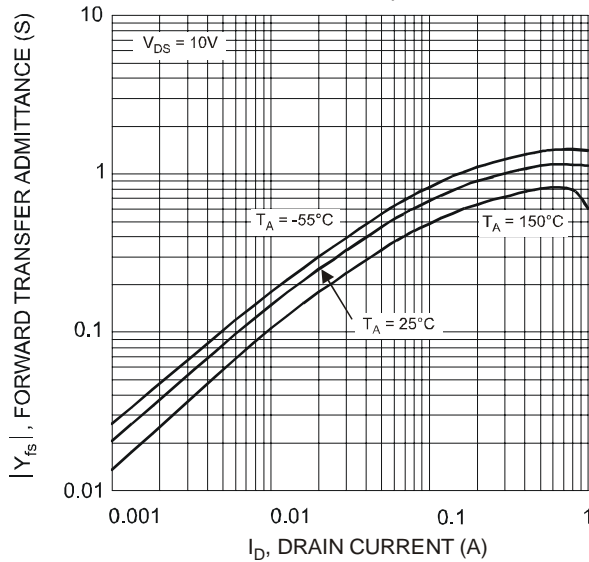


Fig. 9 Forward Transfer Admittance vs. Drain Current

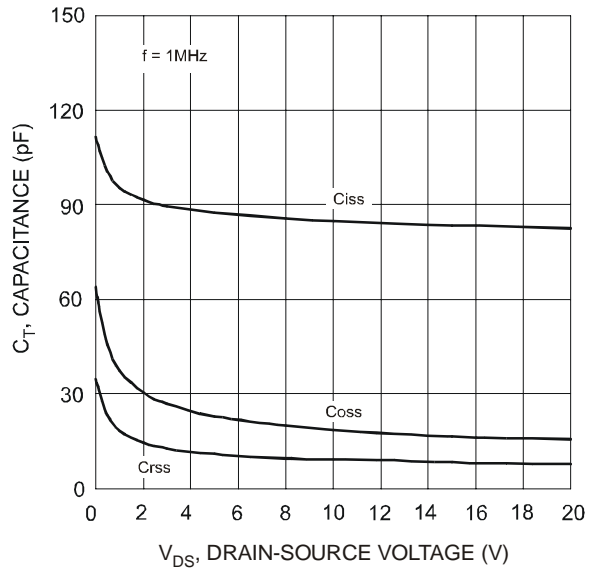


Fig. 10 Typical Capacitance

**Q<sub>2</sub>, P-CHANNEL**

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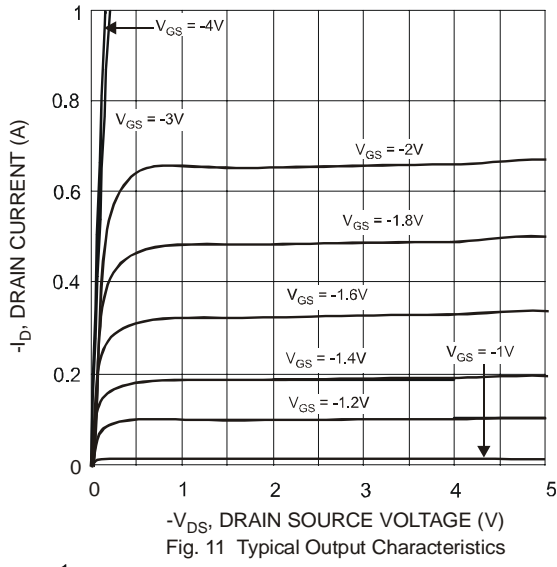


Fig. 11 Typical Output Characteristics

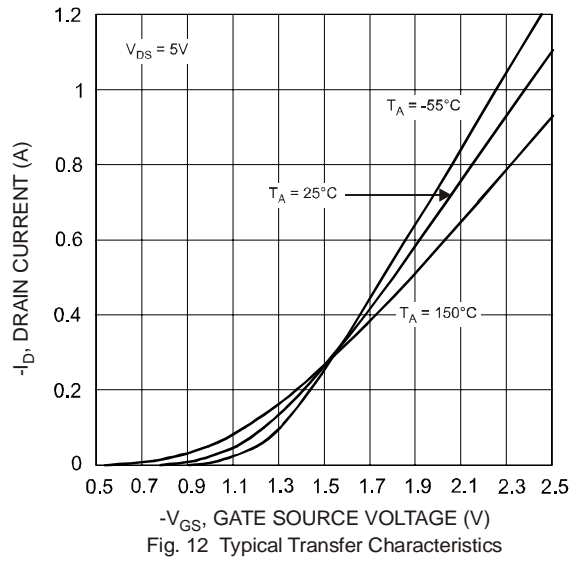


Fig. 12 Typical Transfer Characteristics

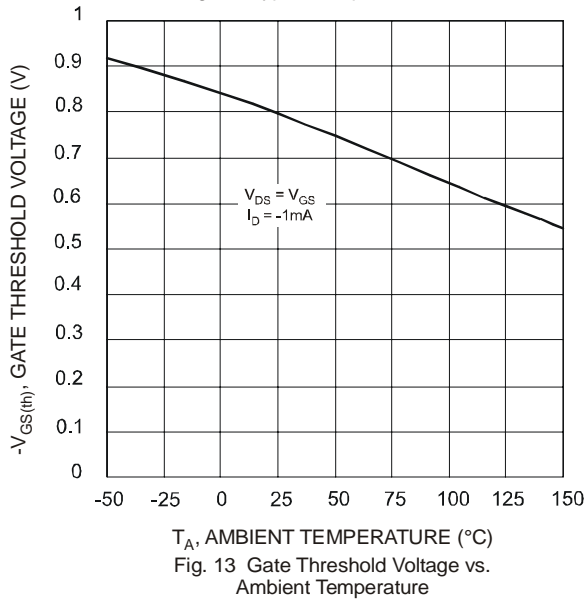


Fig. 13 Gate Threshold Voltage vs. Ambient Temperature

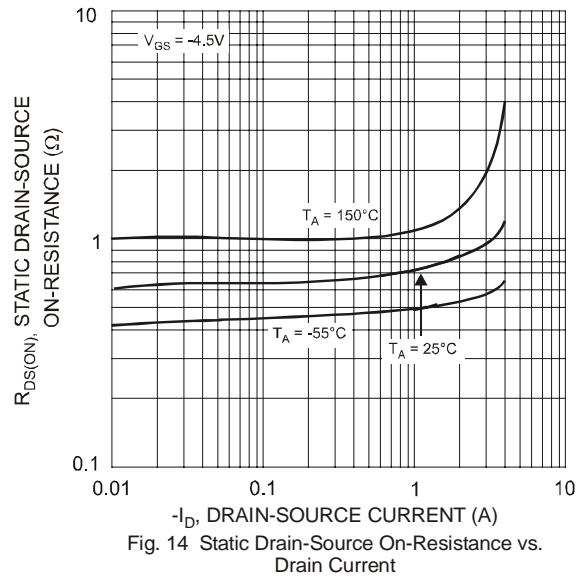


Fig. 14 Static Drain-Source On-Resistance vs. Drain Current

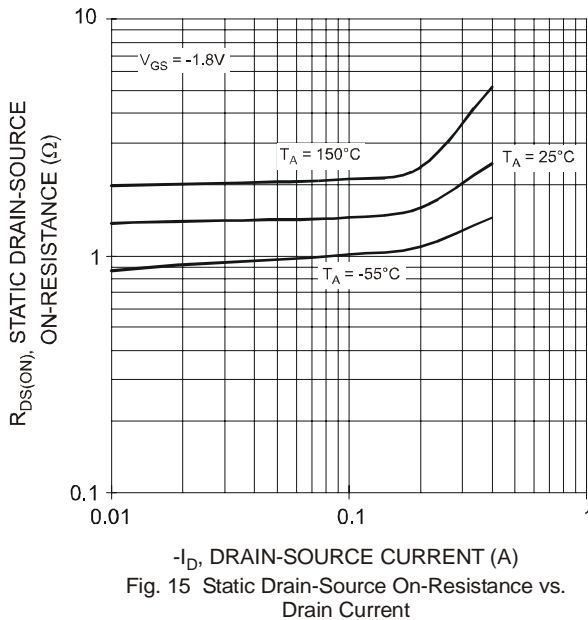


Fig. 15 Static Drain-Source On-Resistance vs. Drain Current

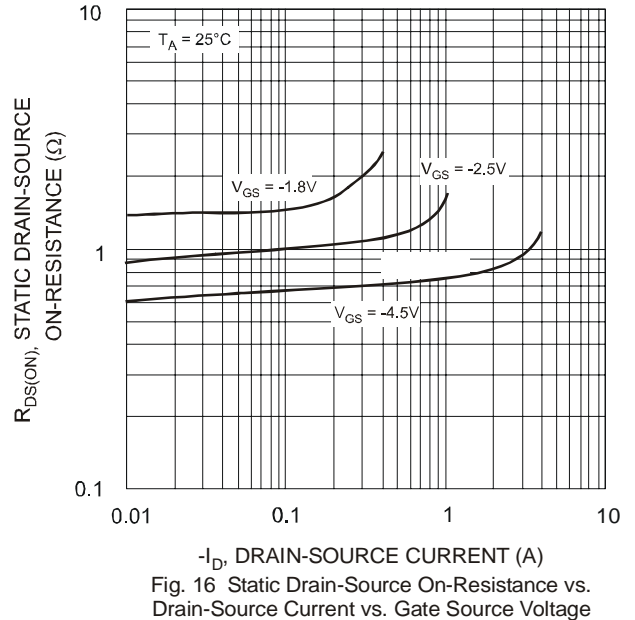


Fig. 16 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

**Q<sub>2</sub>, P-CHANNEL, Continued**

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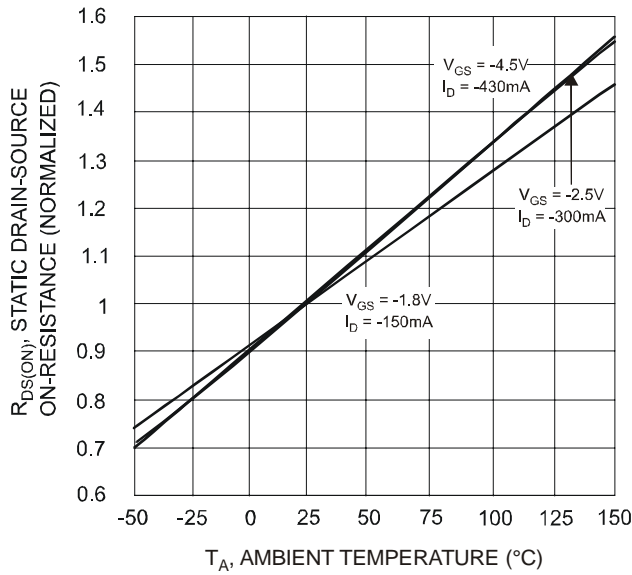


Fig. 17 Static Drain-Source On-State Resistance vs. Ambient Temperature

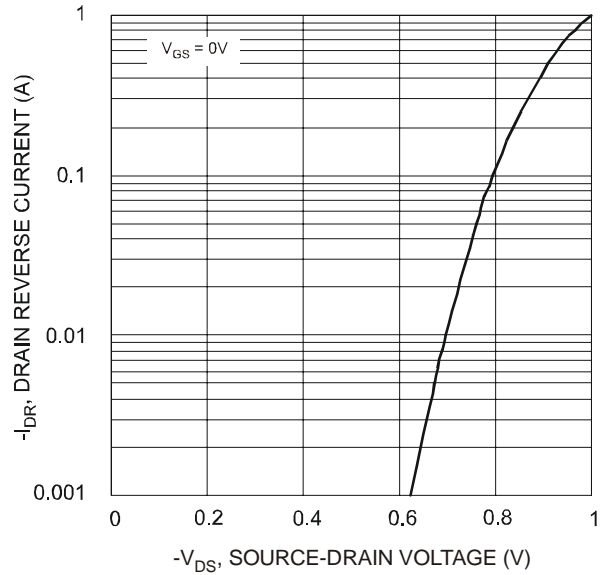


Fig. 18 Reverse Drain Current vs. Source-Drain Voltage

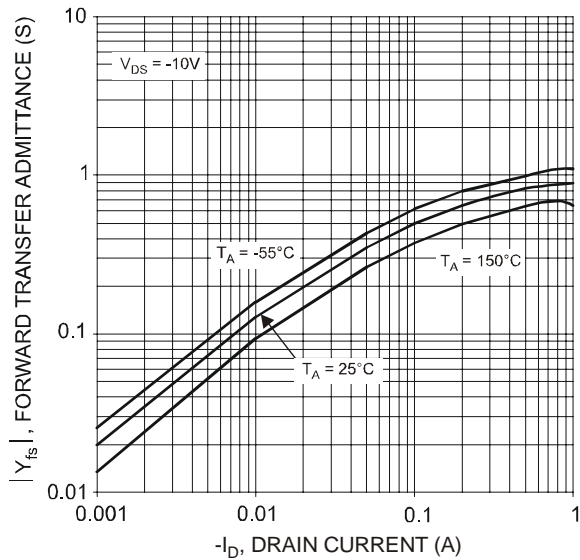


Fig. 19 Forward Transfer Admittance vs. Drain Current

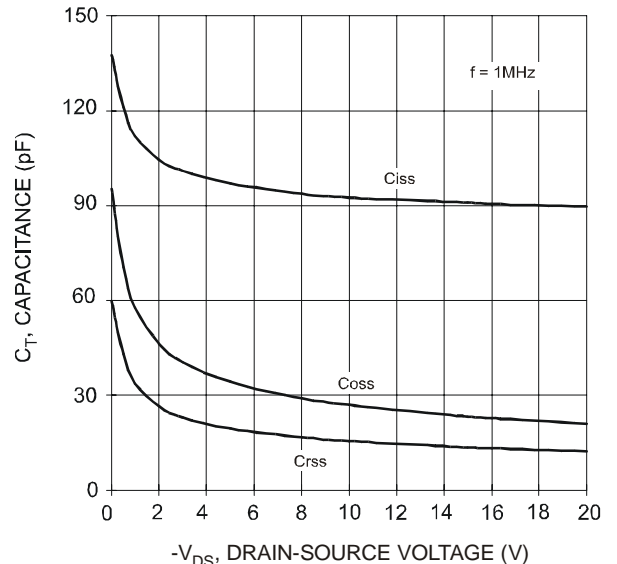


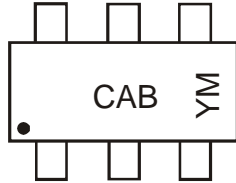
Fig. 20 Typical Capacitance

**Ordering Information** (Note 5)

Part Number	Case	Packaging
DMC2004DWK-7	SOT-363	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



CAB = Marking Code  
 YM = Date Code Marking  
 Y = Year ex: U = 2007  
 M = Month ex: 9 = September

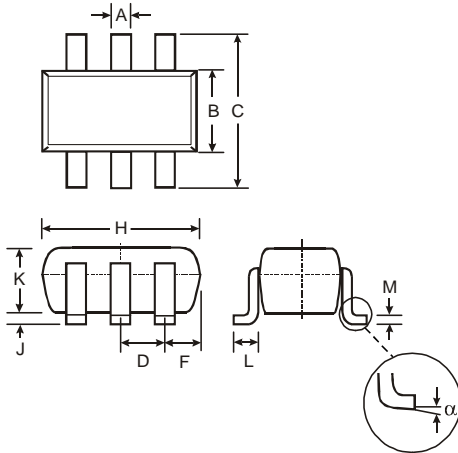
Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

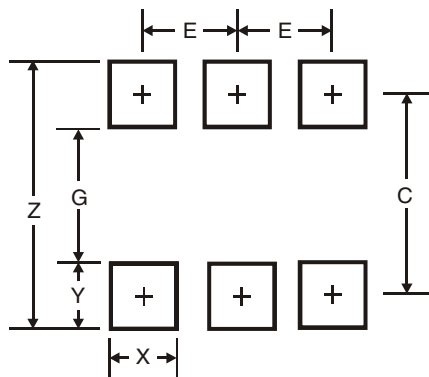
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
$\alpha$	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C	1.9
E	0.65

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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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